VRW-56 QSQ Silicon NPN transistor in a SOT-23 Plastic Package.

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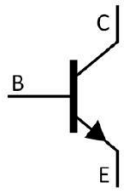
High f_T ,low collector to base time constant, low output capacitance.

For use as UHF oscillator and a UHF mixer in a turner of a TV receiver.





PIN1 Base PIN 2 Emitter PIN 3 Collector

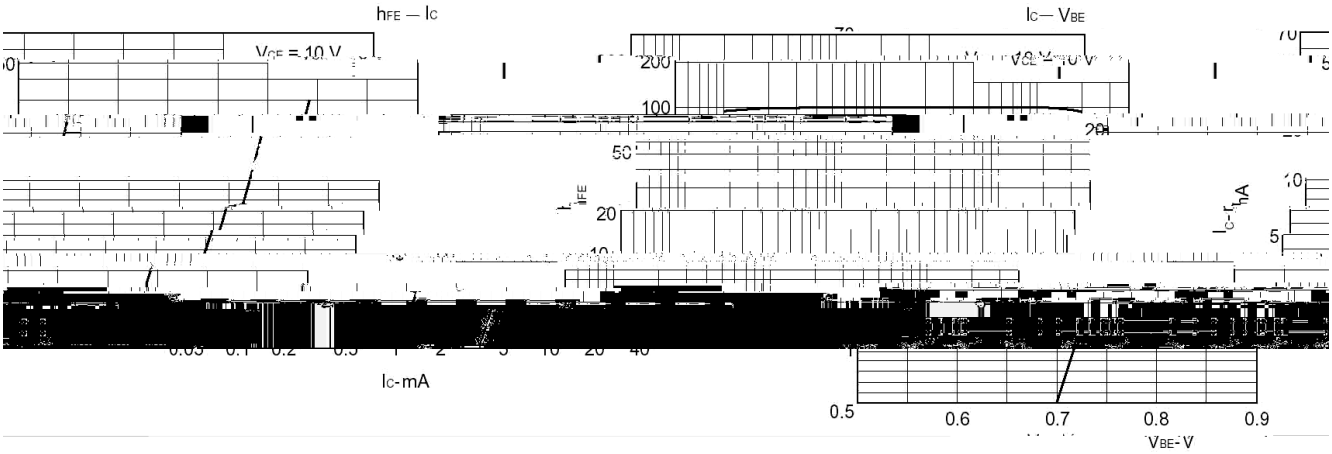
/ h_{FE} Classifications & Marking

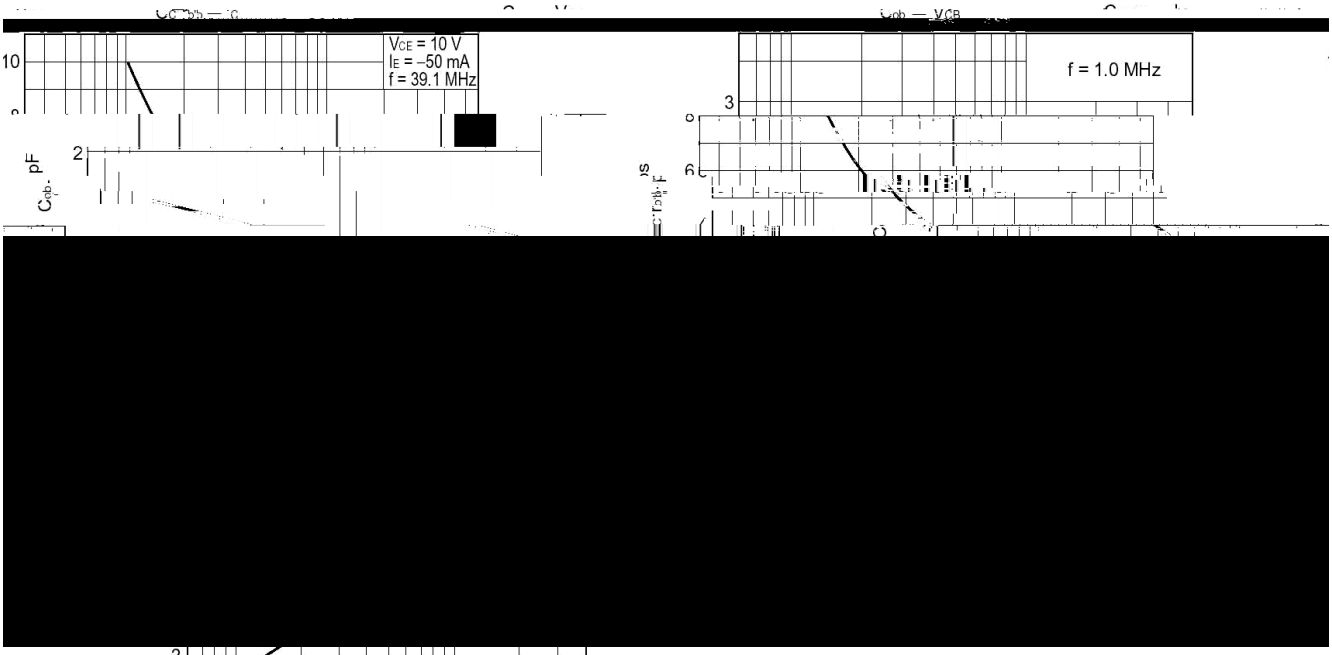
h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	40 80	60 120	100 200
Marking	HT62	HT63	HT64

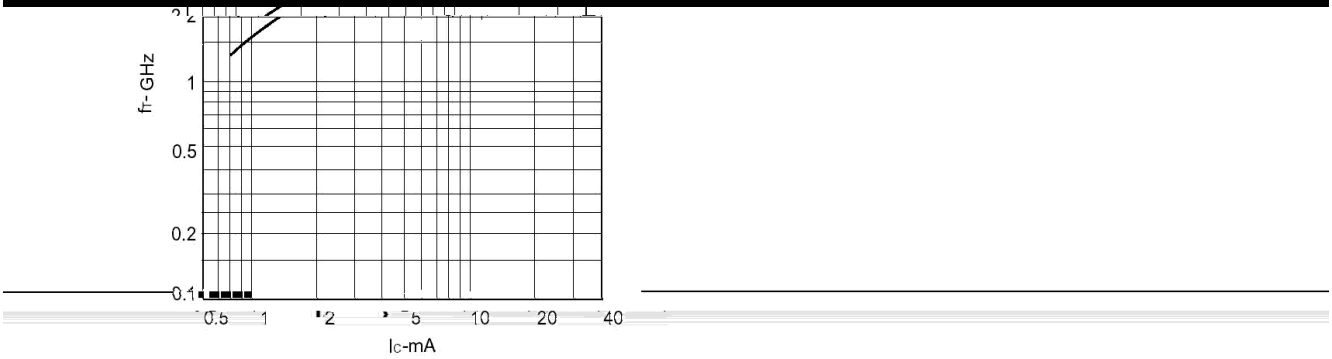
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	25	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	30	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=10V I_E=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=10V I_C=5.0mA	40	100	200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10mA I_B=1.0mA		0.09	0.5	V
Transition Frequency	f_T	V_{CE}=10V I_E=-5.0mA	2.5	4.0		GHz

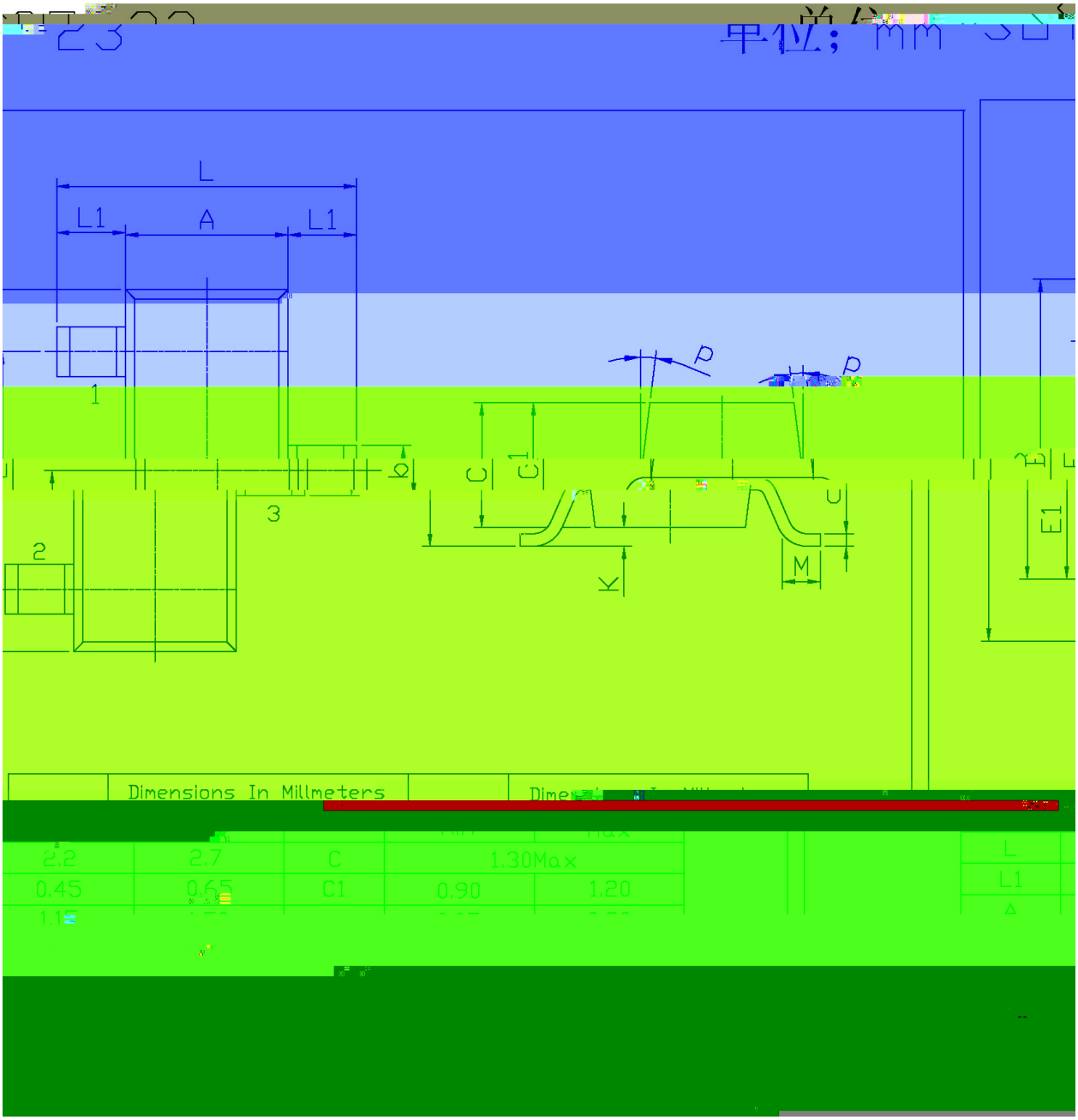
/ Electrical Characteristic Curve



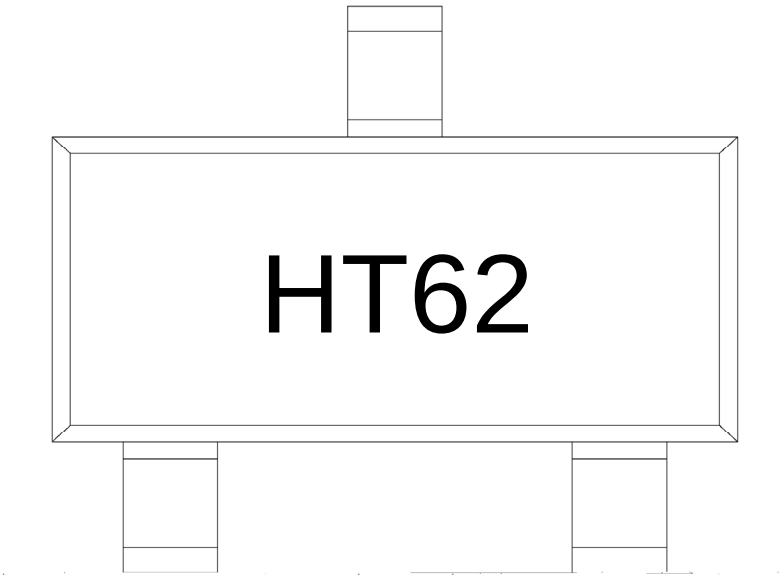




/ Package Dimensions



/ Marking Instructions

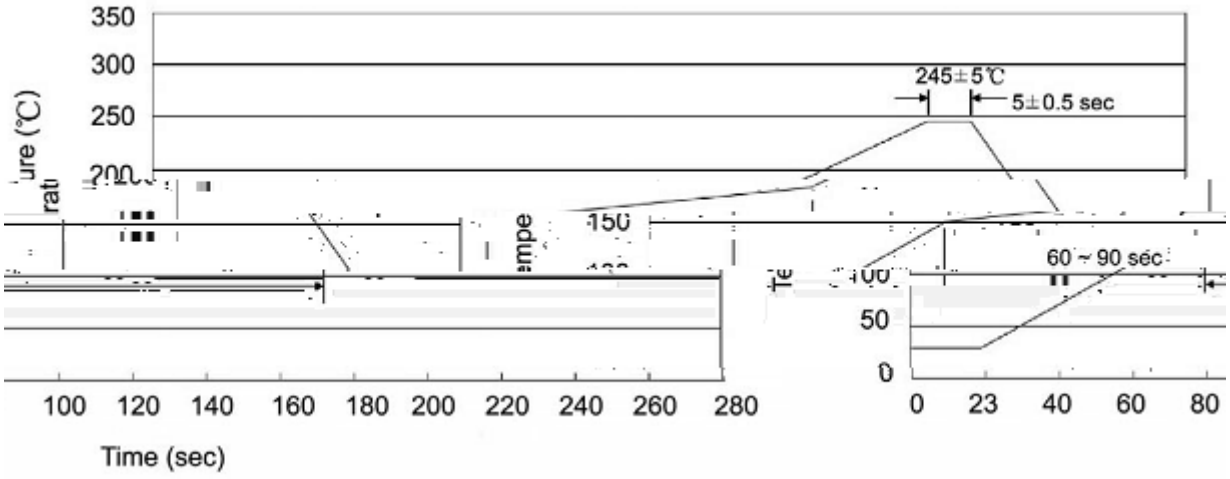


H	И
W65	N

Note:

H	Company Code
W65	Product Type Code

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec;

2 245±5 5±0.5sec;

3 2 10 /sec.

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:245±5 , Duration:5±0.5sec.

3.